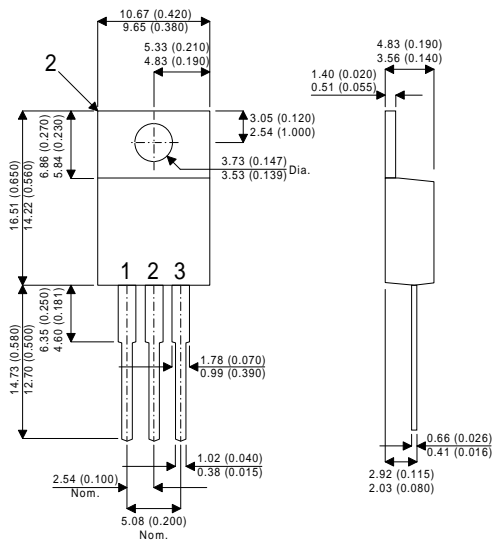


TO220-AC Package Outline.  
Dimensions in mm (inches)



**N-CHANNEL  
ENHANCEMENT MODE  
HIGH VOLTAGE  
ISOLATED  
POWER MOSFETS**

**$V_{DSS}$  1500V**  
 **$I_{D(cont)}$  0.1A**  
 **$R_{DS(on)}$  140Ω**

Pin 1 – Gate      Pin 2 – Drain      Pin 3 – Source

**ABSOLUTE MAXIMUM RATINGS** ( $T_{AMB} = 25^{\circ}C$  unless otherwise stated)

$V_{DSS}$	Drain – Source Voltage	1500	V
$I_D$	Continuous Drain Current	0.1	A
$I_{DM}$	Pulsed Drain Current	0.2	A
$V_{GS}$	Gate – Source Voltage	±20	V
$P_D$	Total Power Dissipation	20	W
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

**ELECTRICAL CHARACTERISTICS** ( $T_{AMB} = 25^{\circ}C$  unless otherwise stated)

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain – Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1mA$	1500			V
$R_{DS(ON)}$	Drain – Source On State Resistance	$V_{GS} = 10V, I_D = 50mA$		140	200	Ω
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 1200V, V_{GS} = 0V$			100	μA
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA
$V_{GS(off)}$	Cutoff Voltage	$V_{DS} = 10V, I_D = 1.0mA$	1.5		3.5	V
$C_{iss}$	Input Capacitance	$V_{DS} = 20V$ $f = 1MHz$		40		pF
$C_{oss}$	Output Capacitance			12		
$C_{rss}$	Reverse Transfer Capacitance			3.0		
$t_{on}$	Turn-on Time	$V_{GS} = 10V$		40		ns
$t_{off}$	Turn-off Time	$I_D = 50mA$		400		
$V_{SD}$	Diode Forward Voltage	$V_{GS} = 0, I_S = 0.1A$		1.0	1.5	V
$ Y_{FS} $	Forward Transfer Admittance	$V_{DS} = 20V, I_D = 50mA$	50	100		mS